

# Measurement Report : Bonn Irradiated sensors

Pradeep Ghosh

## 1. Description of Sensors

- Sensors : FSD 01 Sensors (From CiS)
- Structure : Bo4nx type
- Schottky Contact width : Yes , 18um
- Passivation on Schottky : Open
- Guard rings : Single side only
- Biasing : punch + poly
- Width of poly resistor : 5um
- Number of Sensors : 4 ( Four )
- Irradiated Sensors : 3 ( namely 1E11, 1E12 and 1E13 )
- Power bonds : On all for Bulk IV and CV measurement.

## 2. Measured values for Sensors

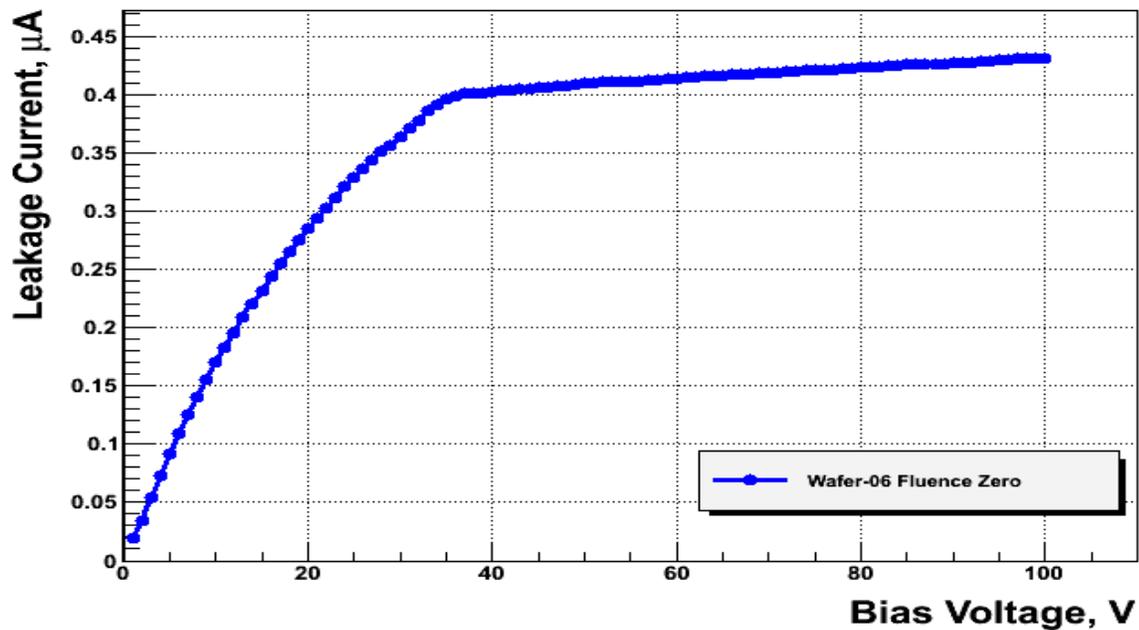
Bo4nx Wafer #	Fluence $n_{eq}/cm^2$	Full Depletion Voltage		Breakdown Volatge	Bulk Capcittance, pF	Expected Operating voltage
		$V_{FD(IV)}$	$V_{FD(CV)}$	$V_{BD}$	$C_{Bulk}$	$V_{OP}$
06	0,00E+00	35 V	~35 V	NO <sup>s</sup> till 100V	100pF	~70V
01	1,00E+11	NO <sup>s</sup>	~40 V	NO <sup>s</sup> till 100V	100pF	~80V
07	1,00E+12	NO <sup>s</sup>	~30 V	NO <sup>s</sup> till 100V	200pF	~60V
10	1,00E+13	NO <sup>s</sup>	~70 V	NO <sup>s</sup> till 100V	230pF	~140V

Note=> NO<sup>s</sup> : Not Observed, See the IV & CV Plots below in Section 3 & 4 for more details.

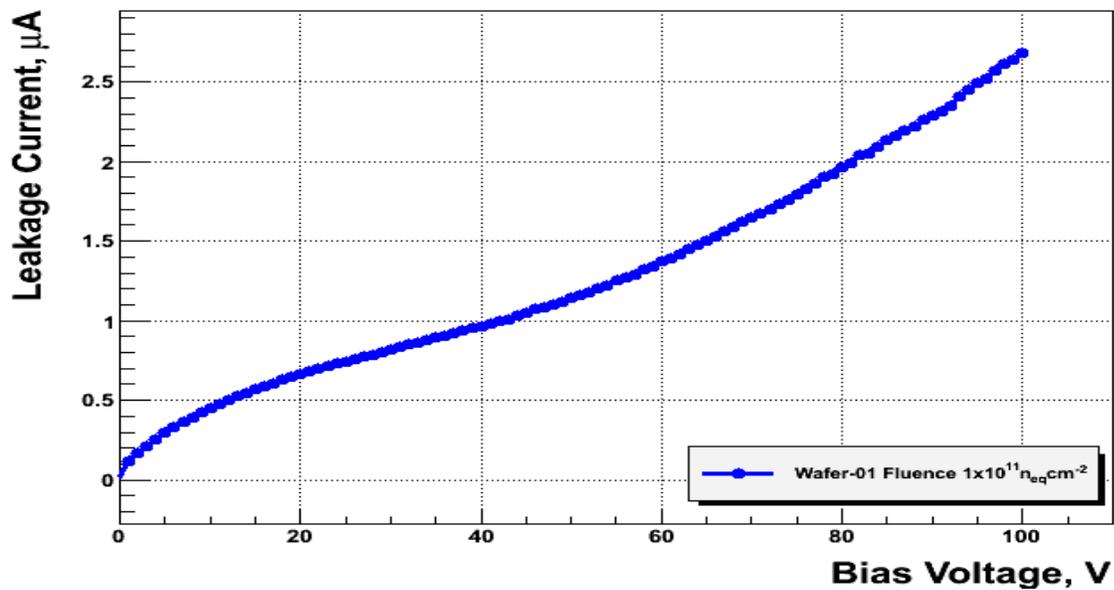
### 3. Plots for IV Curves

The IV measurement was done using Keithley 6487 source meter and associated LabVIEW program upto 100V for all the sensors.

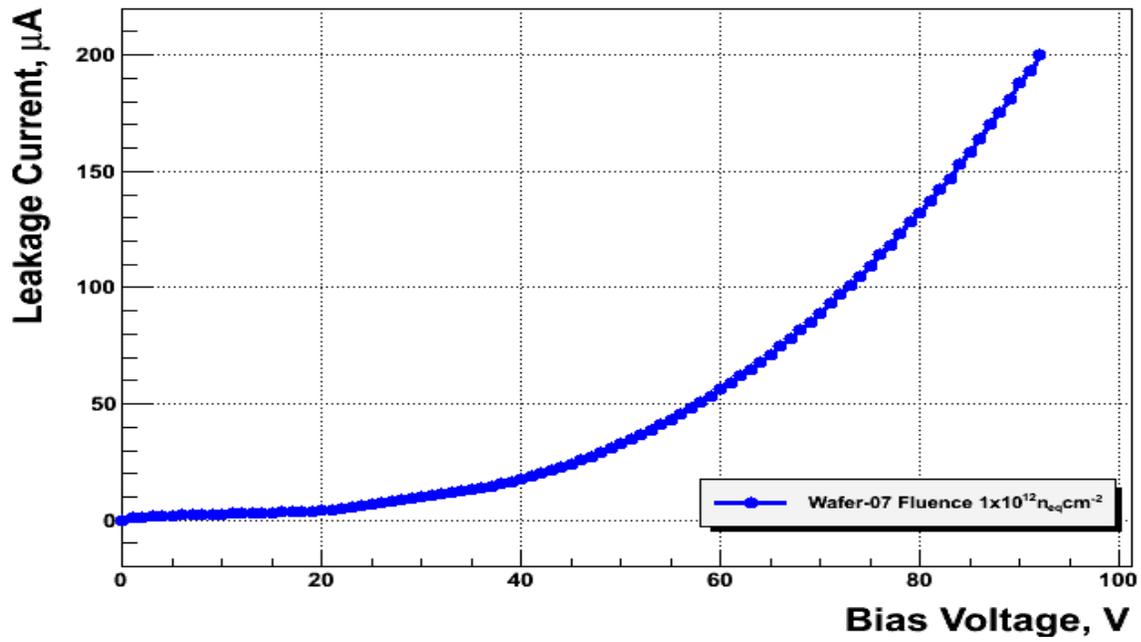
#### 3.1 Wafer 06 bo4nx Zero Fluence



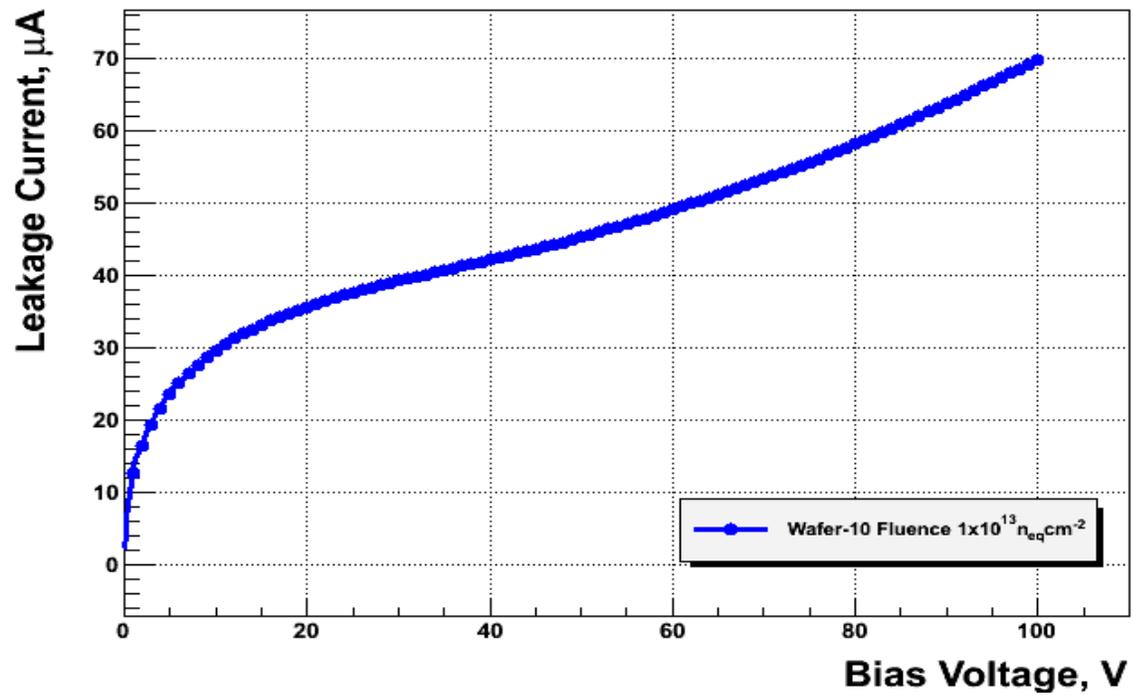
#### 3.2 Wafer 01 bo4nx Fluence $1E11n_{eq}/cm^2$



### 3.3 Wafer 07 bo4nx Fluence $1E12n_{eq}/cm^2$



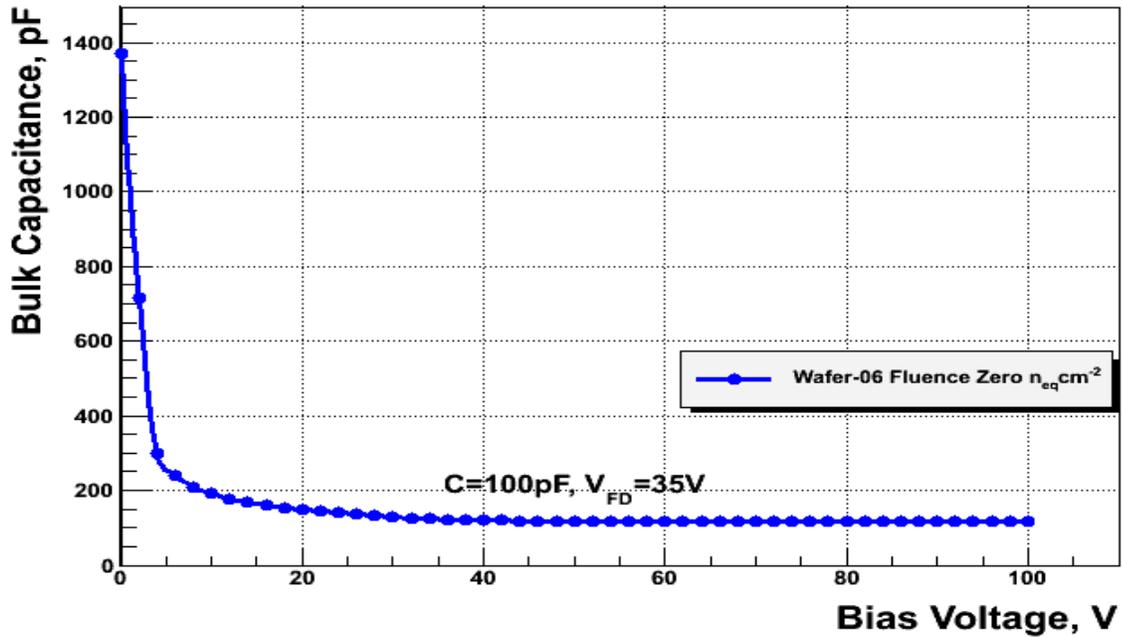
### 3.4 Wafer 10 bo4nx Fluence $1E13n_{eq}/cm^2$



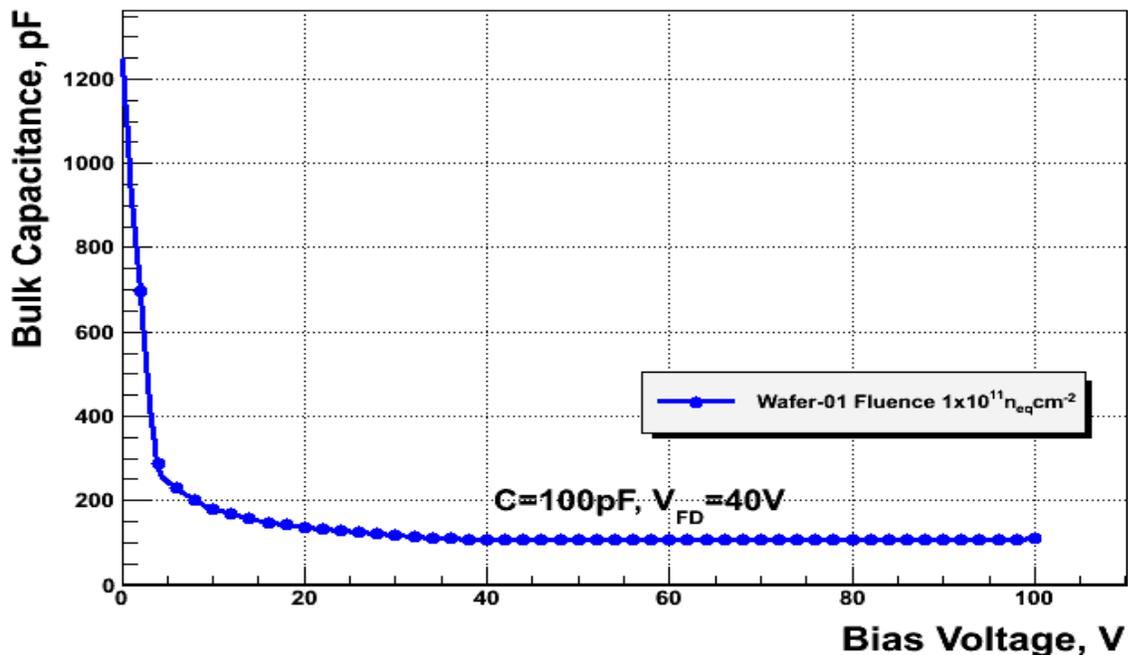
#### 4. Plots for CV Curves

The CV measurement was done using Keithley 6487 source meter and associated LabVIEW program at 5kHz frequency till 100V for all the sensors.

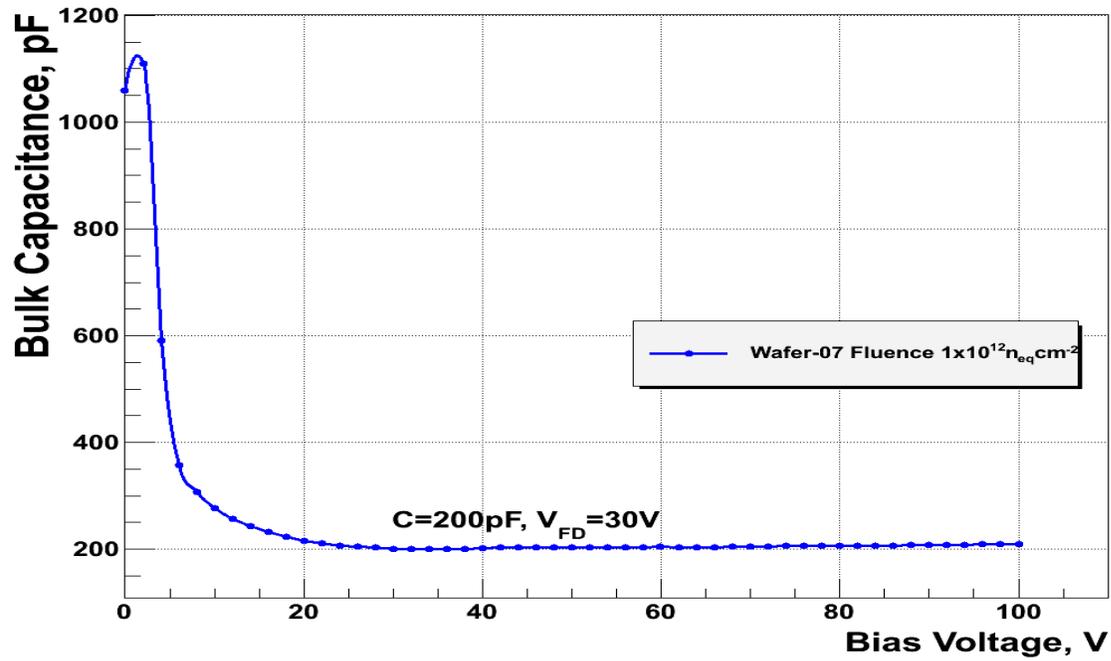
##### 4.1 Wafer 06 bo4nx Zero Fluence



##### 4.2 Wafer 01 bo4nx Fluence $1E11 n_{eq}/cm^2$



#### 4.3 Wafer 07bo4nx Fluence $1E12$ $n_{eq}/cm^2$



#### 4.4 Wafer 10 bo4nx Fluence $1E13$ $n_{eq}/cm^2$

